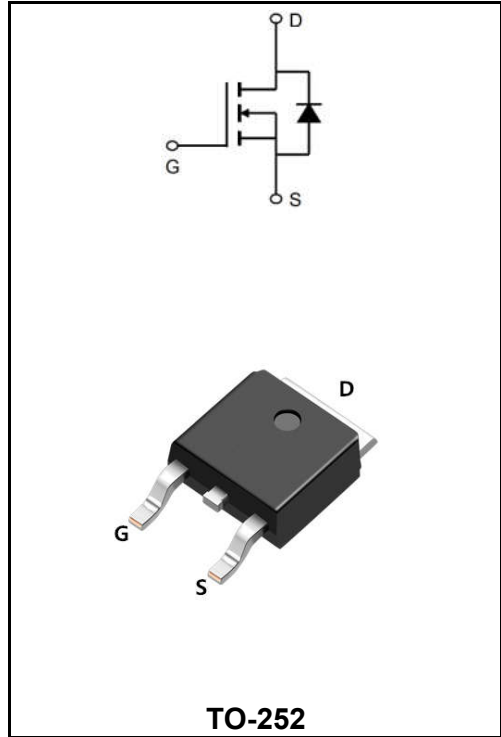


30V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	60A
V_{DSS}	30V
$R_{DS(on)-typ}(@V_{GS}=10V)$	< 8.5mΩ (Type:6.0 mΩ)



Application

- ◆VBUS
- ◆Wireless impact
- ◆Mobile phone fast charging



Product Specification Classification

Part Number	Package	Marking	Pack
YFW60N03AD	TO-252	YFW 60N03AD XXXXX	2500PCS/Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	30	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current, $V_{GS} @ 10V^1 @ T_C=25^\circ C$	I_D	60	A
Continuous Drain Current, $V_{GS} @ 10V^1 @ T_C=100^\circ C$	I_D	40	A
Pulsed Drain Current ²	I_{DM}	92	A
Single Pulse Avalanche Energy ³	E_{AS}	57.8	mJ
Avalanche Current	I_{AS}	34	A
Total Power Dissipation ⁴ @Tc=25°C	P_D	29	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C
Thermal Resistance, Junction-to-Ambient ¹	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	4.32	°C/W

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	BV_{DSS}	30	33	-	V
Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=12A$	$R_{DS(ON)}$	-	6.0	8.5	mΩ
	$V_{GS}=4.5V, I_D=10A$		-	8.5	13	
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	1.0	1.6	2.5	V
$V_{GS(th)}$ Temperature Coefficient		$\Delta V_{GS(th)}$	-	-5.8	-	mV/°C
Drain -Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ C$	I_{DSS}	-	-	1	μA
	$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ C$		-	-	5	
Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	I_{GSS}	-	-	±100	nA
Forward Transconductance	$V_{DS}=5V, I_D=15A$	g_{FS}	-	9.8	-	S
Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	R_g	-	1.7	-	Ω
Total Gate Charge(4.5V)	$V_{DS}=20V$ $V_{GS}=4.5V$ $I_D=12A$	Q_g	-	12.8	-	nC
Gate-Source Charge		Q_{gs}	-	3.3	-	
Gate-Drain Charge		Q_{gd}	-	6.5	-	
Turn-on delay time	$V_{DD}=12V$ $V_{GS}=10V$ $R_G=3.3\Omega$ $I_D=5A$	$t_{d(on)}$	-	4.5	-	ns
Rise Time		T_r	-	10.8	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	25.5	-	
Fall Time		t_f	-	9.6	-	
Input Capacitance	$V_{DS}=15V$ $V_{GS}=0V$ $f=1.0MHz$	C_{iss}	-	1317	-	pF
Output Capacitance		C_{oss}	-	163	-	
Reverse Transfer Capacitance		C_{rss}	-	131	-	
Continuous Source Current ^{1,5}	$V_G=V_D=0V, \text{ Force Current}$	I_S	-	-	46	A
Pulsed Source Current ^{2,5}		I_{SM}	-	-	92	A
Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	V_{SD}	-	-	1	V

Note :

- 1、 The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width $\cong 300\mu s$, duty cycle $\cong 2\%$
- 3、 The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=34A$
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

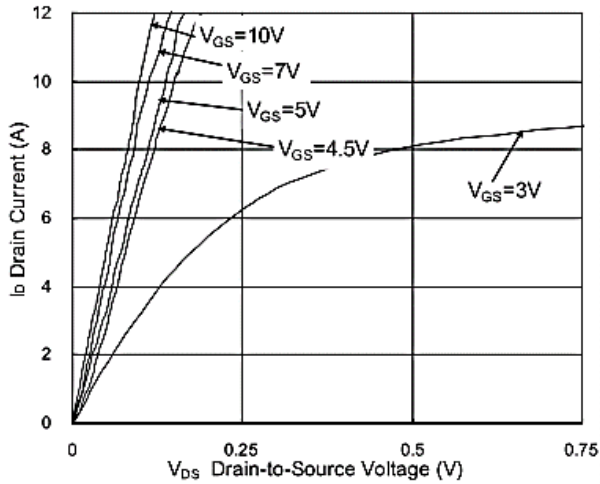


Fig.1 Typical Output Characteristics

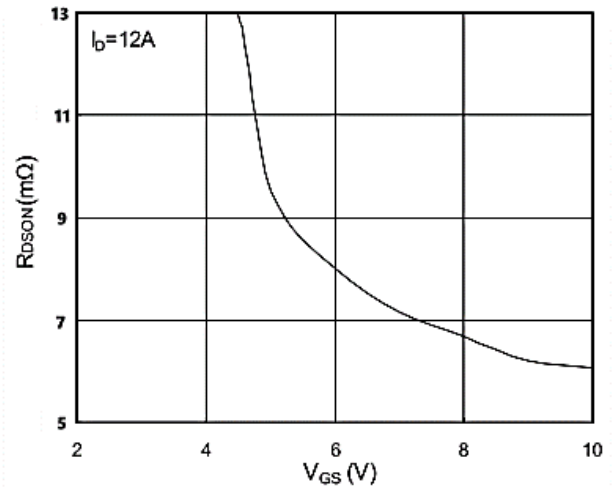


Fig.2 On-Resistance vs. G-S Voltage

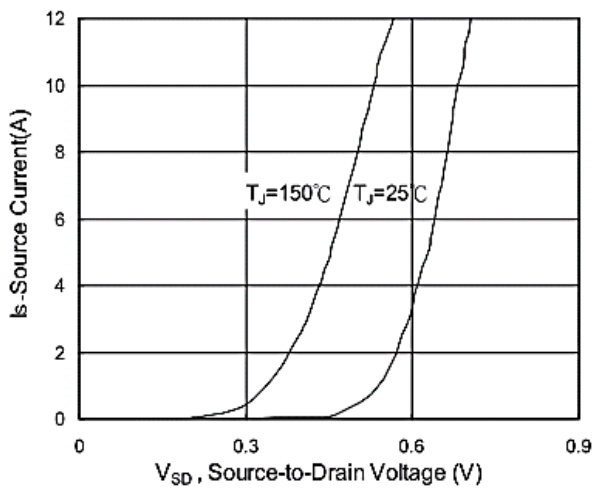


Fig.3 Forward Characteristics of Reverse

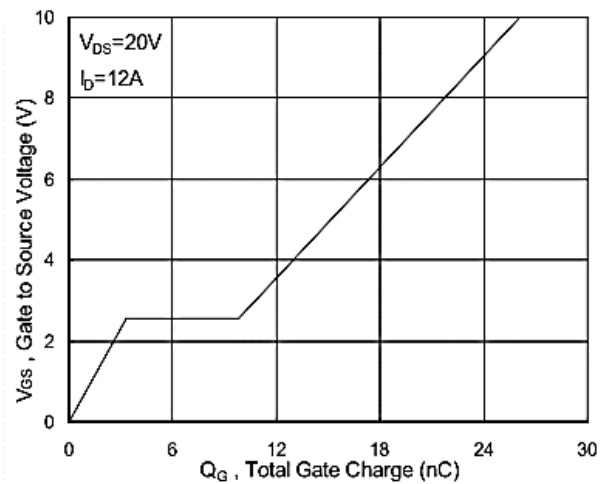


Fig.4 Gate-Charge Characteristics

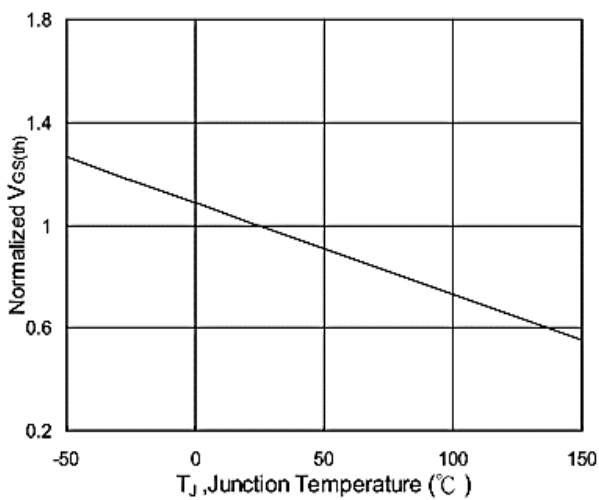


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

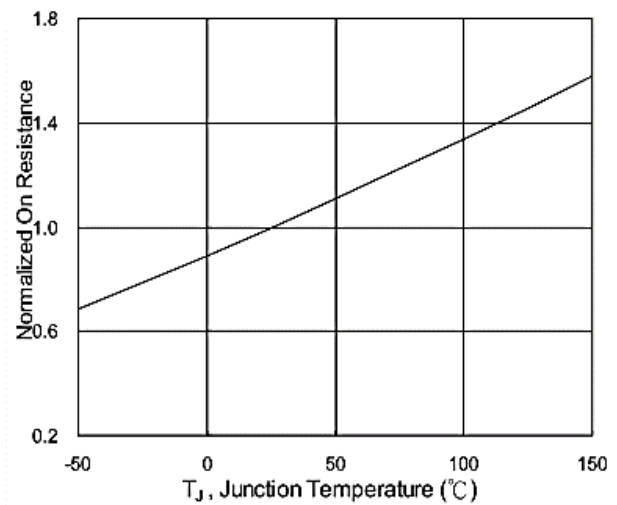


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Ratings and Characteristic Curves

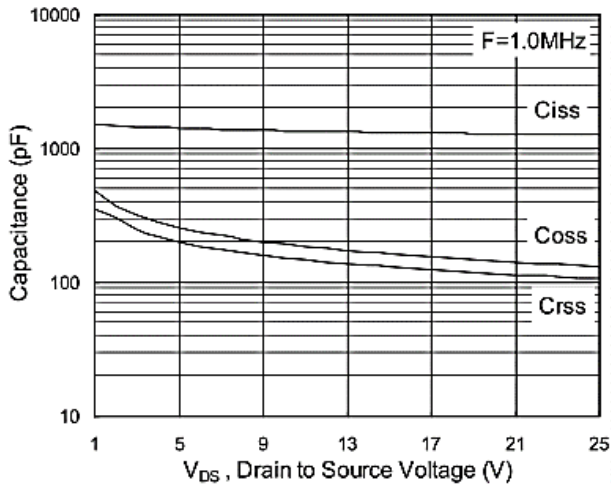


Fig.7 Capacitance

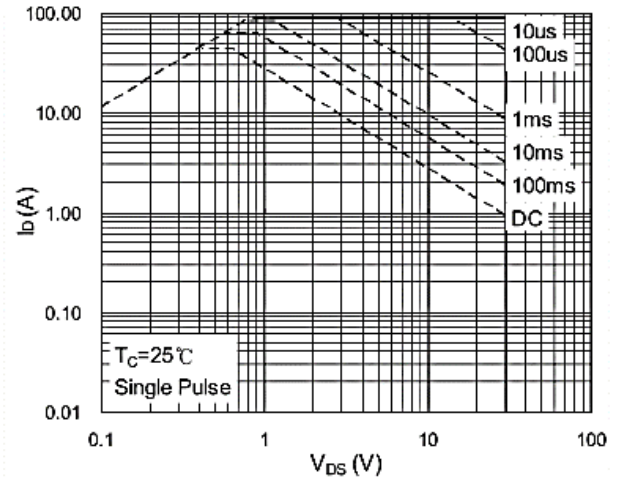


Fig.8 Safe Operating Area

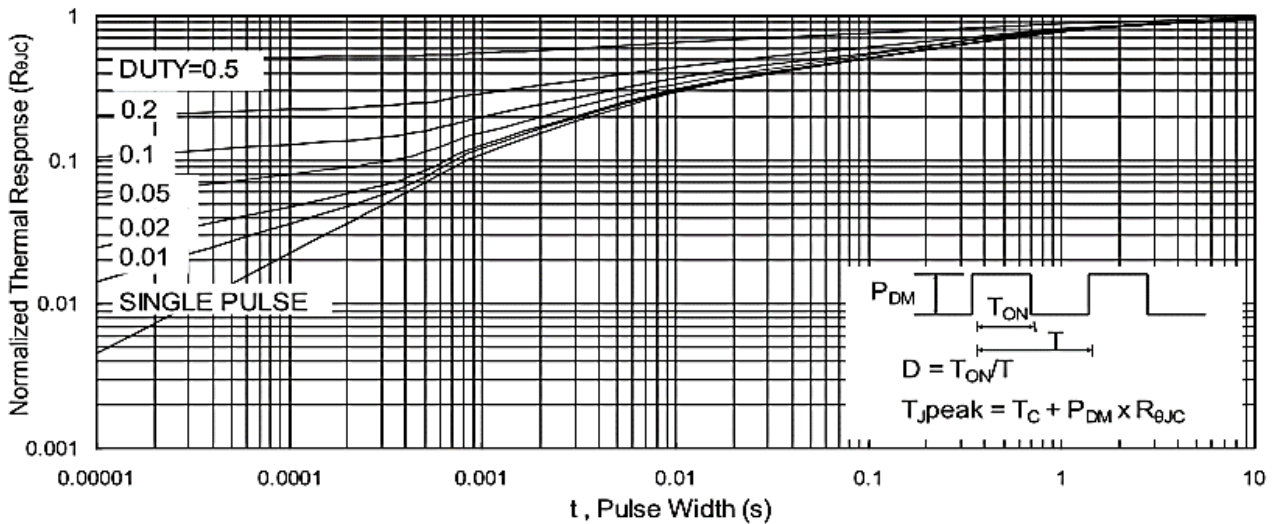


Fig.9 Normalized Maximum Transient Thermal Impedance

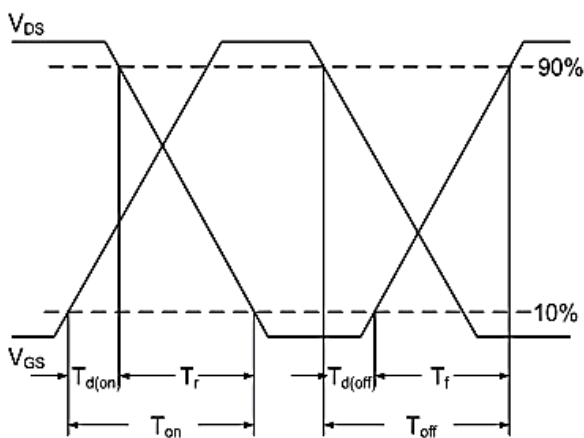


Fig.10 Switching Time Waveform

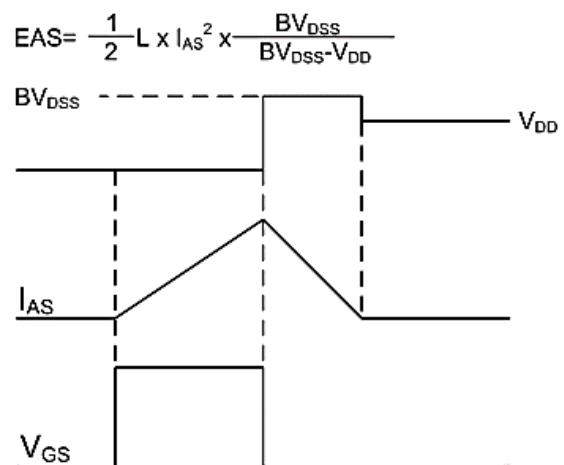
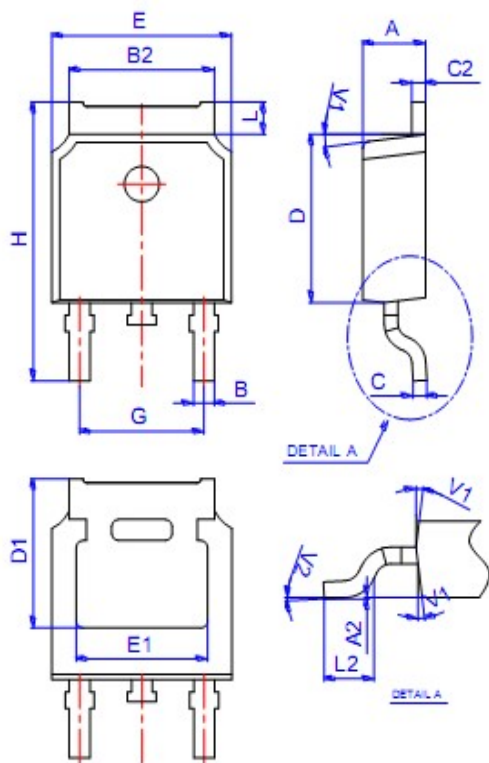


Fig.11 Unclamped Inductive Switching Waveform

Package Outline Dimensions Millimeters

TO-252

Dim.	Min.	Typ.	Max.
A	2.10	-	2.50
A2	0	-	0.10
B	0.66	-	0.86
B2	5.18	-	5.48
C	0.40	-	0.60
C2	0.44	-	0.58
D	5.90	-	6.30
D1	5.30REF		
E	6.40	-	6.80
E1	4.63	-	-
G	4.47	-	4.67
H	9.50	-	10.70
L	1.09	-	1.21
L2	1.35	-	1.65
V1	-	7°	-
V2	0°	-	6°
All Dimensions in millimeter			



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